

U.S.S.N. 10,656,585

IN THE CLAIMS

Please cancel claims 1,4 and 21-30 without prejudice.

Please amend claims 2,5,31 and 34.

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Listing of Claims

1. (cancelled)

2. (currently amended) The apparatus of claim ~~1~~ 31 wherein said ingot consists essentially of a material selected from the group consisting of copper, silicon dioxide and tantalum.

3. (cancelled)

4. (cancelled)

5. (currently amended) The apparatus of claim ~~1~~ 31 wherein said pre-conditioning arm comprises a support and an ingot mount head carried by said support, and wherein said ingot is carried by said ingot mount head.

6. (previously presented) The apparatus of claim 5 wherein said ingot consists essentially of a material selected from the group consisting of copper, silicon dioxide and tantalum.

7 - 30. (cancelled)

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31. (currently amended) A polishing apparatus for condition and pre-conditioning a polishing pad to achieve a desired polishing pad temperature for a semiconductor wafer polishing operation, comprising:

a conditioning arm comprising a conditioning head, said conditioning arm pivotally mounted adjacent the polishing pad for conditioning the polishing pad;

a pre-conditioning arm mounted adjacent the polishing pad; and,

an ingot consisting essentially of a first material, said ingot removeably and fixedly mounted on said pre-conditioning arm for engaging and pre-conditioning the polishing pad, said pre-conditioning arm pivotable for sweeping said ingot across said polishing pad, said ingot for raising a temperature of said polishing pad to a desired operating temperature within a desired time period for polishing a semiconductor production wafer surface comprising said first material;

wherein an actuation mechanism operably engages said

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pre-conditioning arm for selectively moving said ingot into and out of contact with the polishing pad at a selected contact pressure.

32. (previously presented) The apparatus of claim 31, wherein the selected pressure is about 4 to about 5 psi.

33. (previously presented) The apparatus of claim 31, wherein said ingot has a thickness of about 1 to about 10 cm.

34. (currently amended) The apparatus of claim 31, wherein said ingot has a diameter of about 6 to about 8 inches.